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Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT186A "full pack" plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Isolated package
- Low holding current for small load currents and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	25	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 92$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	4	А
Static charact	teristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	4	10	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \frac{\text{Fig. 7}}{\text{C}}$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{\text{Fig. 7}}$	-	11	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	2.2	15	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		sym051
3	G	gate		·
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

6. Ordering information

Table 3. Ordering information

Type number	Package								
	Name	Description	Version						
BT136X-600E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A						
BT136X-600E/DG	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A						

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 92$ °C; Fig. 1; Fig. 2; Fig. 3	-	4	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	25	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	27	А
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	3.1	A ² s
dl _T /dt	rate of rise of on-state current	I _G = 20 mA; T2+ G+	-	50	A/µs
		I _G = 20 mA; T2+ G-	-	50	A/µs
		I _G = 50 mA; T2- G+	-	10	A/µs
		I _G = 20 mA; T2- G-	-	50	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

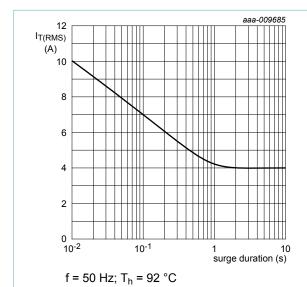


Fig. 1. RMS on-state current as a function of surge duration; maximum values

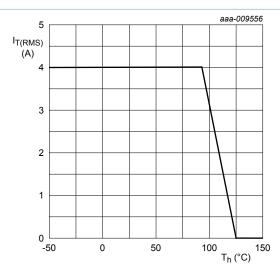


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

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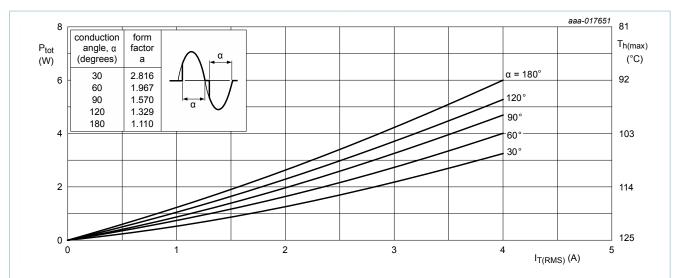
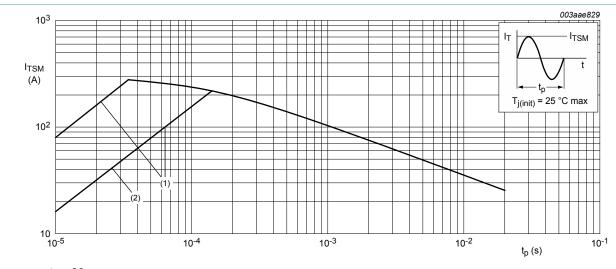


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



- $t_p \le 20 \text{ ms}$
- (1) dI_T/dt limit
- (2) T2- G+ quadrant limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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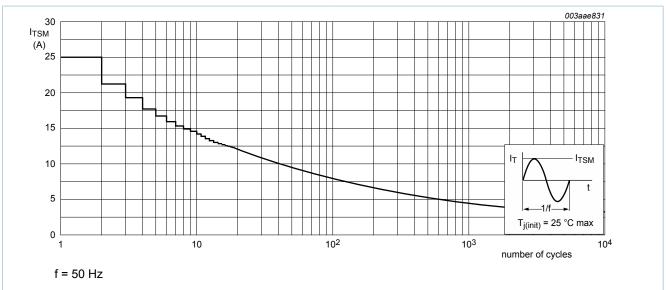


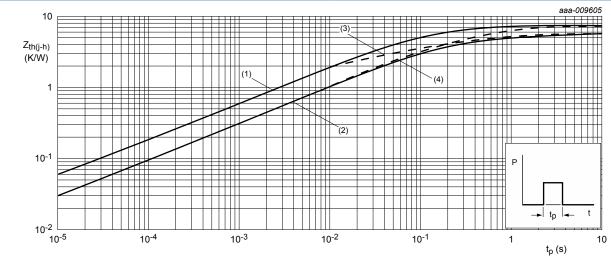
Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig. 6		-	-	5.5	K/W
	heatsink	full or half cycle; without heatsink compound; Fig. 6		-	-	7.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Bidirectional (full cycle) with heatsink compound
- (3) Unidirectional (half cycle) with heatsink compound
- (4) Bidirectional (full cycle) without heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

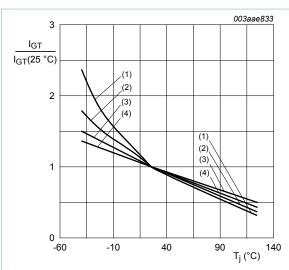
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	11	25	mA
L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	3	15	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8	-	10	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	2.5	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	4	20	mA
н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	2.2	15	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics		l l	-1		
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

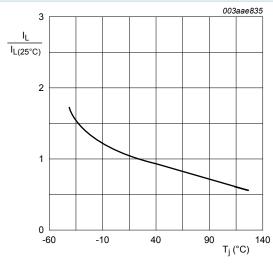


Fig. 8. Normalized latching current as a function of junction temperature

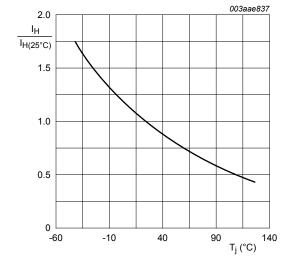
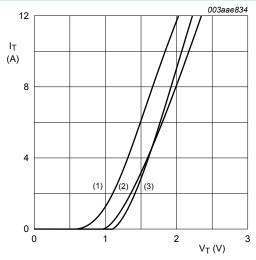


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.27 \text{ V}$

 $R_s = 0.091 \Omega$

(1) T_i = 125 °C; typical values

(2) T_j = 125 °C; maximum values

(3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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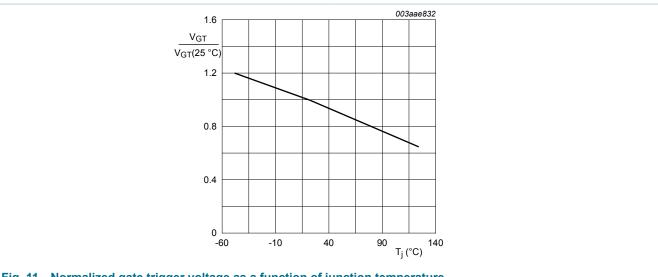
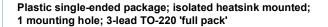


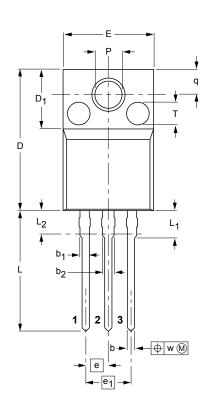
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

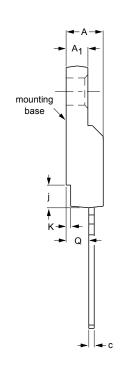
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11. Package outline



SOT186A





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁	b ₂	С	D	D ₁	E	е	e ₁	j	к	L	L ₁	L ₂ ⁽¹⁾ max.	Р	Q	q	T ⁽²⁾	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are # 2.5×0.8 max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT186A		3-lead TO-220F				-02-04-09 06-02-14

Fig. 12. Package outline TO-220F (SOT186A)

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